

INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) Sheet 1 of 2	Atty. Docket No. 22010-135/IL-2-CON2	Serial No. 09/160,657
	Applicant Joseph W. Lyding et al.	
	Filing Date September 25, 1998	Group Art Unit 2811

U.S. PATENT DOCUMENTS

*Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	Filing Date If appropriate
MG	3,849,204	11/19/1974	Fowler	148	1.5	06/29/1973
MG	3,923,559	12/02/1975	Sinha	148	1.5	01/13/1975
MG	4,113,514	09/12/1978	Pankove et al.	148	1.5	01/16/1978
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MG	5,571,339	11/05/1996	Ringel et al.	136	252	04/17/1995
MG	5,693,961	12/02/1997	Hamada	257	66	11/21/1995
MG	5,872,387	02/16/1999	Lyding et al.	257	607	01/16/1996

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
MG	WO 94/19829	09/01/1994	PCT	H01L	29/40, 21/306		X

Examiner

Date Considered

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Examiner Initial	PUBLICATION		
MG	Ph. Avouris, R.E. Walkup, A.R. Rossi, T.-C. Shen, G.C. Abeln, J.R. Tucker and J.W. Lyding, "STM-Induced H Atom Desorption From Si(100): Isotope Effects And Site Selectivity", <i>Chemical Physics Letters</i> , Vol. 257, pp. 148-154 (July 19, 1996).		
MG	G. Ganguly and A. Matsuda, "Light-Induced Defect Densities In Hydrogenated And Deuterated Amorphous Silicon Deposited At Different Substrate Temperatures", <i>Am. Phys. Soc.</i> , Vol. 49, No. 16, pp. 10 986-10 990 (April 15, 1994).		
MG	I.P. Ipatova, O.P. Chikalova-Luzina and K. Hess, "Effect Of Localized Vibrations On The Si Surface Concentrations Of H And D", <i>J. Appl. Phys.</i> , Vol. 83, No. 2, pp. 814-819 (January 15, 1998).		
MG	J.W. Lyding, T.-C. Shen, G.C. Abeln, C. Wang, E.T. Foley and J.R. Tucker, "Silicon Nanofabrication And Chemical Modification By UHV-STM", <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 380, pp. 187-197 (1995).		
MG	J.C. Mikkelsen, Jr., "Secondary Ion Mass Spectrometry Characterization Of D ₂ O and H ₂ ¹⁸ O Steam Oxidation Of Silicon", <i>J. Electronic Mat.</i> , Vol. 11, No. 3, pp. 541-558 (1982).		
MG	S.M. Myers and P.M. Richards, "Interactions Of Deuterium With Ion-Irradiated SiO ₂ On Si", <i>J. Appl. Phys.</i> , Vol. 67, No. 9, pp. 4064-4071 (May 1, 1990).		
MG	H. Park and C.R. Helms, "The Effect Of Annealing Treatment On The Distribution Of Deuterium In Silicon And In Silicon/Silicon Oxide Systems", <i>J. Electrochem. Soc.</i> , Vol. 139, No. 7, pp. 2042-2046 (July 1992).		
MG	N.S. Saks and R.W. Rendell, "The Time-Dependence Of Post-Irradiation Interface Trap Build-Up In Deuterium-Annealed Oxides", <i>IEEE Transactions On Nuclear Science</i> , Vol. 39, No. 6, pp. 2220-2229 (December 1992).		
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MG	T.-C. Shen, C. Wang, G.C. Abeln, J.R. Tucker, J.W. Lyding, Ph. Avouris and R.E. Walkup, "Atomic-Scale Desorption Through Electronic And Vibrational Excitation Mechanisms", <i>Science</i> , Vol. 268, pp. 1590-1592 (June 16 1995).		
MG	J.M. Zavada, B.L. Weiss, I.V. Bradley, B. Theys, J. Chevallier, R. Rahbi, R. Addinall, R.C. Newman and H.A. Jenkinson, "Optical Waveguides Formed By Deuterium Passivation Of Acceptors In Si Doped p-Type GaAs Epilayers", <i>J. Appl. Phys.</i> , Vol. 71, No. 9, pp. 4151-4155 (May 1, 1992).		
Examiner		Date Considered	
Maria Guerrero		4-28-99	
<small>*Examiner: initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>			